TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS126

February 1998

CD74HC03, CD74HCT03

High Speed CMOS Logic Quad 2-Input NAND Gate with Open Drain

Features

- **Buffered Inputs**
- **Typical Propagation Delay: 8ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C**
- **Output Pull-up to 10V**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The Harris CD74HC03 and CD74HCT03 logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 74HCT logic family is functionally as well as pin compatible with the standard 74LS logic family.

These open drain NAND gates can drive into resistive loads to output voltages as high as 10V. Minimum values of R_L required verses load voltage are shown in Figure 2.

Ordering Information

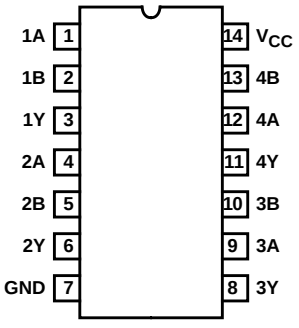
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC03E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT03E	-55 to 125	14 Ld PDIP	E14.3
CD74HC03M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT03M	-55 to 125	14 Ld SOIC	M14.15

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

CD74HC03, CD74HCT03
(PDIP, SOIC)
TOP VIEW



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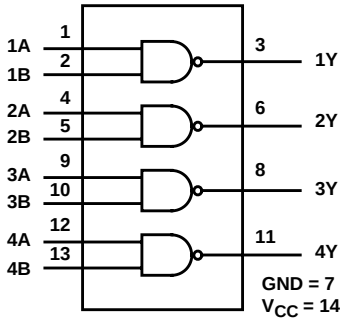
Functional Diagram



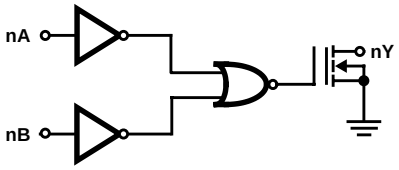
TRUTH TABLE

A	B	Y	
L	L	Z (Note 4)	H (Note 3)
H	L	Z (Note 4)	H (Note 3)
L	H	Z (Note 4)	H (Note 3)
H	H	L	L

NOTES:

3. Requires pull-up (R_L to V_L)
4. Without pull-up (high impedance)

Logic Symbol



Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC Drain Current, per Output, I_O
For -0.5V < V_O . . . . . -25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 5) θ_{JA} (°C/W)
PDIP Package 90
SOIC Package 175
Maximum Junction Temperature (Hermetic Package or Die) . . . 175°C
Maximum Junction Temperature (Plastic Package) . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

5. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	2	-	20	-	40	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads				4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	4	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	2	-	20	-	40	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 6)	V_{CC} - 2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

6. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nA, nB	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, Input to Output (Figure 1)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	100	-	125	-	150	ns
			4.5	-	-	20	-	25	-	30	ns
			6	-	-	17	-	21	-	26	ns
Propagation Delay, Data Input to Output Y	t_{PLH}, t_{PHL}	C_L = 15pF	5	-	8	-	-	-	-	-	ns
Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	18	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 7, 8)	C_{PD}	-	5	-	6.4	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 1)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	24	-	30	-	36	ns
Propagation Delay, Data Input to Output Y	t_{PLH}, t_{PHL}	C_L = 15pF	5	-	9	-	-	-	-	-	ns
Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Power Dissipation Capacitance (Notes 7, 8)	C_{PD}	-	5	-	9	-	-	-	-	-	pF

NOTES:

7. C_{PD} is used to determine the dynamic power consumption, per gate.
8. $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o) + \Sigma (V_L^2/R_L)$ (Duty Factor "Low")
   where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, V_{CC} = supply voltage, Duty Factor "Low" = percent of time output is "low", V_L = output voltage, R_L = pull-up resistor.

Test Circuits and Waveforms

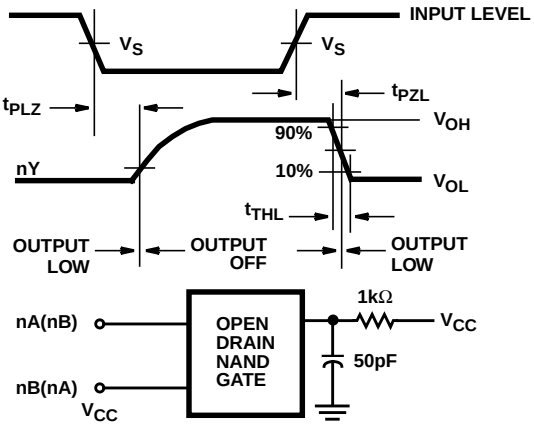


FIGURE 1. TRANSITION TIMES, PROPAGATION DELAY TIMES, AND TEST CIRCUIT

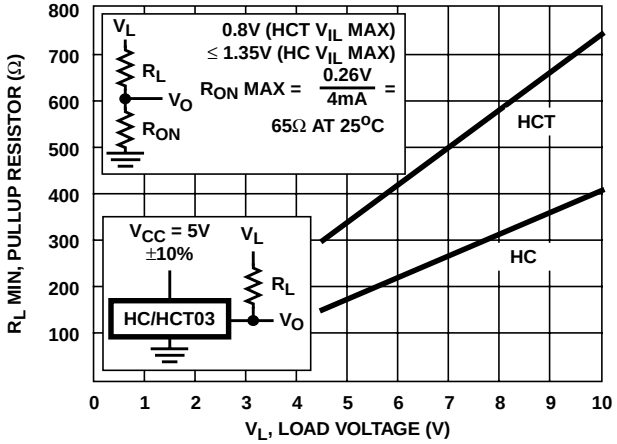


FIGURE 2. MINIMUM RESISTIVE LOAD vs LOAD VOLTAGE

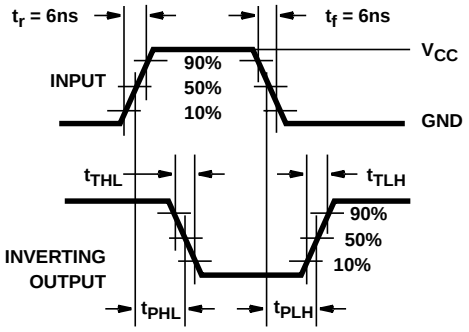


FIGURE 3. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

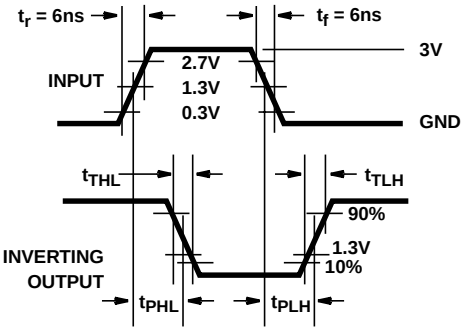


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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